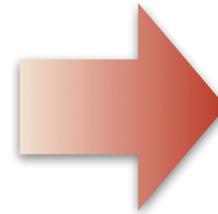


CYGNO parameters

From CYGNUS feasibility paper (in preparation)

He:CF₄ ??

Gas mixture	SF ₆	SF ₆ : ⁴ He
Gas pressure [torr]	20	20:740
W [eV / ion pair]	35.45	?
Transverse diffusion, σ_T [$\mu\text{m} / \sqrt{\text{cm}}$]	116.2	116.2
Longitudinal diffusion, σ_z [$\mu\text{m} / \sqrt{\text{cm}}$]	116.2	116.2
Drift velocity [$\mu\text{m}/\mu\text{s}$]	140	140
z binning (assume 1MHz sampling) [$\mu\text{m}/$]	140	140
Avalanche gain	9000	9000

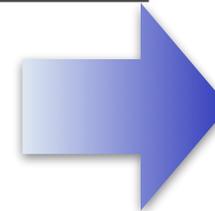


450:300
40 eV
xx
xx
61000 num/mus
61/100 num
80000 ph/primary e
8 ph/e-

Factor 1000 is assumed for photon loss due to $1/r^2$

PMT + CMOS?

Readout type	Dimensionality	Segmentation (x × y)	Capacitance [pF]	σ_{noise} in 1 μs [e ⁻]	Threshold/ σ_{noise}
planar	1D (z)	10 cm × 10 cm	3000	18000	3.09
wire	2D (yz)	1 m wires, 2 mm pitch		800	4.11
pad	1D (z)	3 mm × 3 mm	0.25 (FIXME)	375	4.77
optical	2D (xy)	200 μm × 200 μm	n/a	20 photons	5.77
strip	3D (xyz)	1 m strips, 200 μm pitch	500	2800	4.61
pixel	3D (xyz)	200 μm × 200 μm	0.012 - 0.200	42	5.77



Optic **3D** **165 x 165 um2** **n/a** **1.3** **6**